



No.5321

2SC5265

NPN Triple Diffused Planar Silicon Transistor

Inverter-controlled Lighting Applications

Features

- High breakdown voltage ($V_{CBO} = 1200V$).
- High reliability (Adoption of HVP process).
- Adoption of MBIT process.

Absolute Maximum Ratings at $T_a = 25^\circ C$

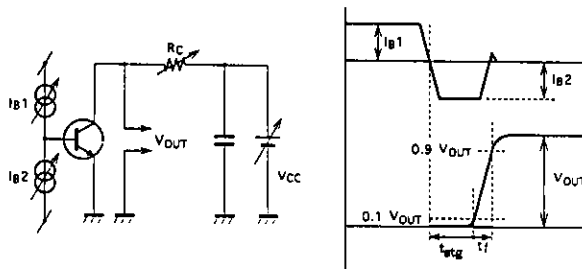
			unit
Collector-to-Base Voltage	V_{CBO}	1200	V
Collector-to-Emitter Voltage	V_{CEO}	600	V
Emitter-to-Base Voltage	V_{EBO}	9	V
Collector Current	I_C	4	A
Collector Current (Pulse)	I_{CP}	8	A
Collector Dissipation	P_C	2	W
		30	W
		150	$^\circ C$
Junction Temperature	T_j		
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

$T_c = 25^\circ C$

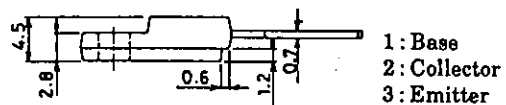
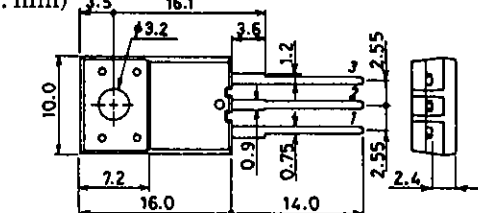
Electrical Characteristics at $T_a = 25^\circ C$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 600V, I_E = 0$			10	μA
Collector Cutoff Current	I_{CES}	$V_{CE} = 1200V, R_{BE} = 0$			1.0	mA
Collector Sustain Voltage	$V_{CEO(sus)}$	$I_C = 100mA, I_B = 0$	600			V
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 9V, I_C = 0$			1.0	mA
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 2.0A, I_B = 0.4A$			1.0	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 2.0A, I_B = 0.4A$			1.5	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = 5V, I_C = 0.3A$	30	40	50	
	$h_{FE(2)}$	$V_{CE} = 5V, I_C = 1.5A$	10			
Storage Time	t_{stg}	$I_C = 2.0A, I_{B1} = 0.4A, I_{B2} = -0.8A$			2.5	μs
Fall Time	t_f	$I_C = 2.0A, I_{B1} = 0.4A, I_{B2} = -0.8A$			0.15	μs

Switching Time Test Circuit



Package Dimensions 2079B
(unit : mm)



- 1 : Base
- 2 : Collector
- 3 : Emitter

SANYO : TO-220FI(LS)

SANYO Electric Co., Ltd. Semiconductor Business Headquarters
TOKYO OFFICE Tokyo Bldg. 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

